Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H1266

APPLICATIONS

General Purpose Application.
Switching Application.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……400mW

V_{CBO}——Collector-Base Voltage……-50V

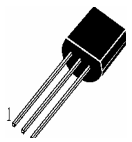
V_{CEO}——Collector-Emitter Voltage……-50V

V_{EBO}——Emitter-Base Voltage……-5V

I_C——Collector Current……-150mA

Ib——Base Current……-50mA

TO-92



1—Emitter，E
2—Collector，C
3—Base，B

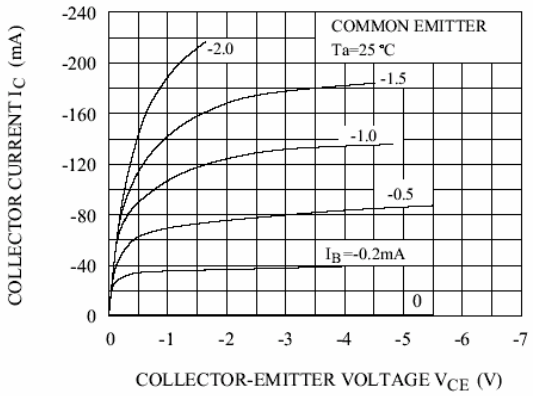
ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-50			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-50			V	I_C=-1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-10μA, I_C=0
H_{FE}（1）	DC Current Gain	70		400		V_{CE}=-6V, I_C=-2mA
H_{FE}（2）	DC Current Gain	25				V_{CE}=-6V, I_C=-150mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.1	-0.3	V	I_C=-100mA, I_B=-10mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			-1.1	V	I_C=-100mA, I_B=-10mA
I_{CBO}	Collector Cut-off Current			-100	nA	V_{CB}=-50V, I_E=0
I_{EBO}	Emitter Cut-off Current			-100	nA	V_{EB}=-5V, I_C=0
f_T	Current Gain-Bandwidth Product	80			MHz	V_{CE}=-10V, I_C=-10mA
Cob	Output Capacitance		4	7	pF	V_{CB}=-50V, I_E=0，f=1MHz

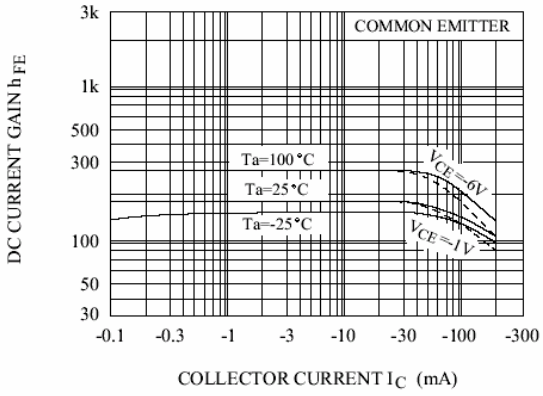
h_{FE} Classification

O	Y	GR
70—140	120—240	200—400

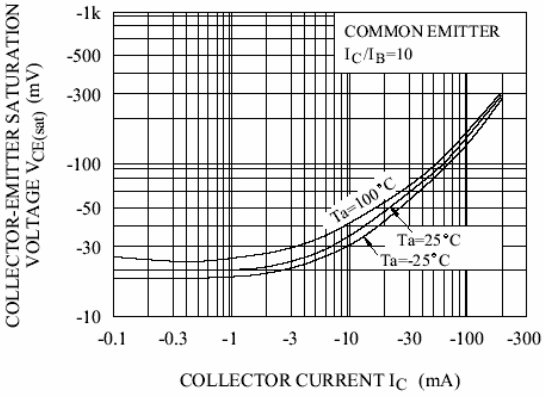
I_C - V_{CE}



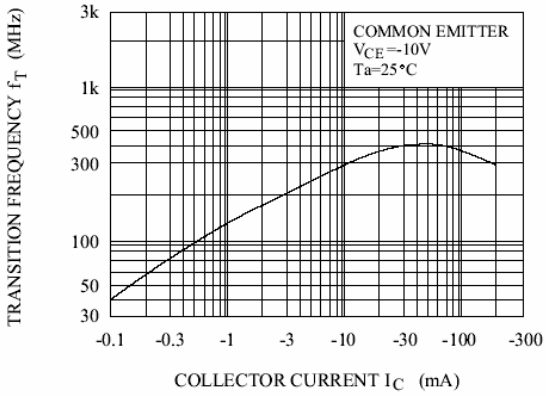
h_{FE} - I_C



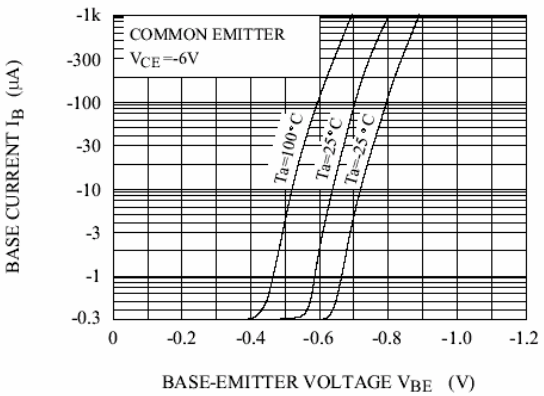
$V_{CE(sat)}$ - I_C



f_T - I_C



I_B - V_{BE}



Pc - Ta